

# NTD32N06L

## Power MOSFET 32 Amps, 60 Volts Logic Level, N-Channel DPAK

Designed for low voltage, high speed switching applications in power supplies, converters and power motor controls and bridge circuits.

### Features

- Smaller Package than MTB30N06VL
- Lower  $R_{DS(on)}$ ,  $V_{DS(on)}$ , and Total Gate Charge
- Lower and Tighter  $V_{SD}$
- Lower Diode Reverse Recovery Time
- Lower Reverse Recovery Stored Charge
- Pb-Free Packages are Available

### Typical Applications

- Power Supplies
- Converters
- Power Motor Controls
- Bridge Circuits

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	60	Vdc
Drain-to-Gate Voltage ( $R_{GS} = 10\text{ M}\Omega$ )	$V_{DGR}$	60	Vdc
Gate-to-Source Voltage - Continuous - Non-Repetitive ( $t_p \leq 10\text{ ms}$ )	$V_{GS}$ $V_{GS}$	$\pm 20$ $\pm 30$	Vdc
Drain Current - Continuous @ $T_A = 25^\circ\text{C}$ - Continuous @ $T_A = 100^\circ\text{C}$ - Single Pulse ( $t_p \leq 10\text{ }\mu\text{s}$ )	$I_D$ $I_D$ $I_{DM}$	32 22 90	Adc Adc Apk
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	93.75 0.625	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 1)		2.88	W
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 2)		1.5	W
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy - Starting $T_J = 25^\circ\text{C}$ (Note 3) ( $V_{DD} = 50\text{ Vdc}$ , $V_{GS} = 5\text{ Vdc}$ , $L = 1.0\text{ mH}$ , $I_{L(pk)} = 25\text{ A}$ , $V_{DS} = 60\text{ Vdc}$ , $R_G = 25\text{ }\Omega$ )	$E_{AS}$	313	mJ
Thermal Resistance - Junction-to-Case - Junction-to-Ambient (Note 1) - Junction-to-Ambient (Note 2)	$R_{\theta JC}$ $R_{\theta JA}$ $R_{\theta JA}$	1.6 52 100	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, 1/8 in from case for 10 seconds	$T_L$	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

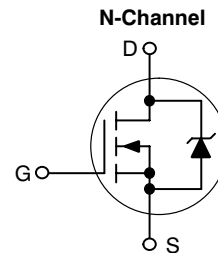
1. When surface mounted to FR4 board using 0.5 in pad size.
2. When surface mounted to FR4 board using minimum recommended pad size.
3. Repetitive rating; pulse width limited by maximum junction temperature.



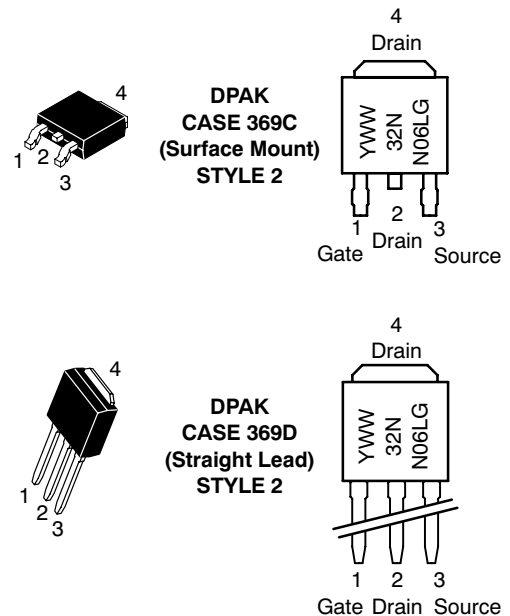
ON Semiconductor®

<http://onsemi.com>

$V_{DS}$	$R_{DS(on)}$ TYP	$I_D$ MAX
60 V	23.7 m $\Omega$	32 A



### MARKING DIAGRAMS & PIN ASSIGNMENTS



Y = Year  
WW = Work Week  
32N06L = Device Code  
G = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# NTD32N06L

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit	
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (Note 4) (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 250 μAdc) Temperature Coefficient (Positive)	V <sub>(BR)DSS</sub>	60 -	70 62	- -	Vdc mV/°C	
Zero Gate Voltage Drain Current (V <sub>DS</sub> = 60 Vdc, V <sub>GS</sub> = 0 Vdc) (V <sub>DS</sub> = 60 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 150°C)	I <sub>DSS</sub>	- -	- -	1.0 10	μAdc	
Gate-Body Leakage Current (V <sub>GS</sub> = ±20 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	-	-	±100	nAdc	
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage (Note 4) (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μAdc) Threshold Temperature Coefficient (Negative)	V <sub>GS(th)</sub>	1.0 -	1.7 4.8	2.0 -	Vdc mV/°C	
Static Drain-to-Source On-Resistance (Note 4) (V <sub>GS</sub> = 5 Vdc, I <sub>D</sub> = 16 Adc)	R <sub>DS(on)</sub>	-	23.7	28	mΩ	
Static Drain-to-Source On-Resistance (Note 4) (V <sub>GS</sub> = 5 Vdc, I <sub>D</sub> = 20 Adc) (V <sub>GS</sub> = 5 Vdc, I <sub>D</sub> = 32 Adc) (V <sub>GS</sub> = 5 Vdc, I <sub>D</sub> = 16 Adc, T <sub>J</sub> = 150°C)	V <sub>DS(on)</sub>	- - -	0.48 0.78 0.61	0.67 - -	Vdc	
Forward Transconductance (Note 4) (V <sub>DS</sub> = 6 Vdc, I <sub>D</sub> = 16 Adc)	g <sub>FS</sub>	-	27	-	mhos	
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>iss</sub>	-	1214	pF	
Output Capacitance		C <sub>oss</sub>	-	343		
Transfer Capacitance		C <sub>rss</sub>	-	87		
SWITCHING CHARACTERISTICS (Note 5)						
Turn-On Delay Time	(V <sub>DD</sub> = 30 Vdc, I <sub>D</sub> = 32 Adc, V <sub>GS</sub> = 5 Vdc, R <sub>G</sub> = 9.1 Ω) (Note 4)	t <sub>d(on)</sub>	-	12.8	ns	
Rise Time		t <sub>r</sub>	-	221		
Turn-Off Delay Time		t <sub>d(off)</sub>	-	37		
Fall Time		t <sub>f</sub>	-	128		
Gate Charge	(V <sub>DS</sub> = 48 Vdc, I <sub>D</sub> = 32 Adc, V <sub>GS</sub> = 5 Vdc) (Note 4)	Q <sub>T</sub>	-	23	nC	
		Q <sub>1</sub>	-	4.5		
		Q <sub>2</sub>	-	14		
SOURCE-DRAIN DIODE CHARACTERISTICS						
Forward On-Voltage	(I <sub>S</sub> = 20 Adc, V <sub>GS</sub> = 0 Vdc) (Note 4) (I <sub>S</sub> = 32 Adc, V <sub>GS</sub> = 0 Vdc) (Note 4) (I <sub>S</sub> = 20 Adc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 150°C)	V <sub>SD</sub>	- - -	0.89 0.95 0.74	1.0 - -	Vdc
Reverse Recovery Time	(I <sub>S</sub> = 32 Adc, V <sub>GS</sub> = 0 Vdc, dI <sub>S</sub> /dt = 100 A/μs) (Note 4)	t <sub>rr</sub>	-	56	ns	
		t <sub>a</sub>	-	31		
		t <sub>b</sub>	-	25		
Reverse Recovery Stored Charge		Q <sub>RR</sub>	-	0.093	-	μC

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

## ORDERING INFORMATION

Device	Package	Shipping†
NTD32N06L	DPAK	75 Units / Rail
NTD32N06LG	DPAK (Pb-Free)	75 Units / Rail
NTD32N06L-1	DPAK (Straight Lead)	75 Units / Rail
NTD32N06L-1G	DPAK (Straight Lead) (Pb-Free)	75 Units / Rail
NTD32N06LT4	DPAK	2500 Units / Tape & Reel
NTD32N06LT4G	DPAK (Pb-Free)	2500 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTD32N06L

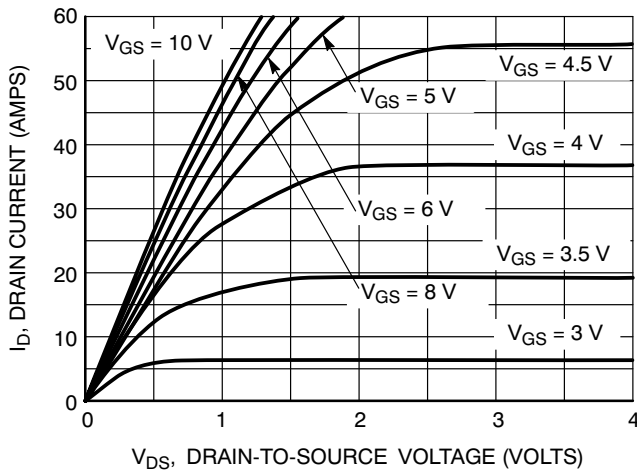


Figure 1. On-Region Characteristics

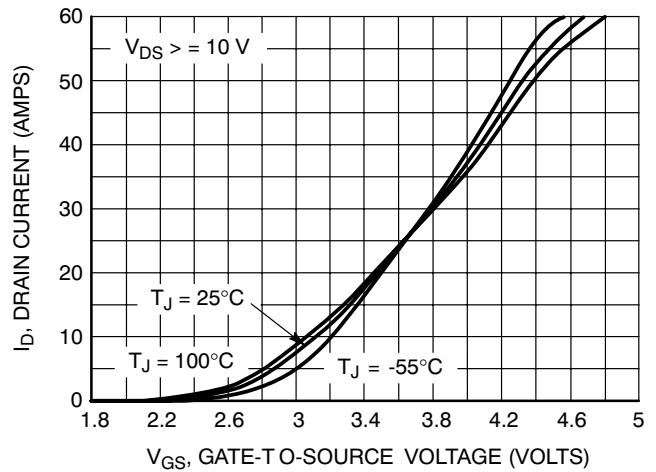


Figure 2. Transfer Characteristics

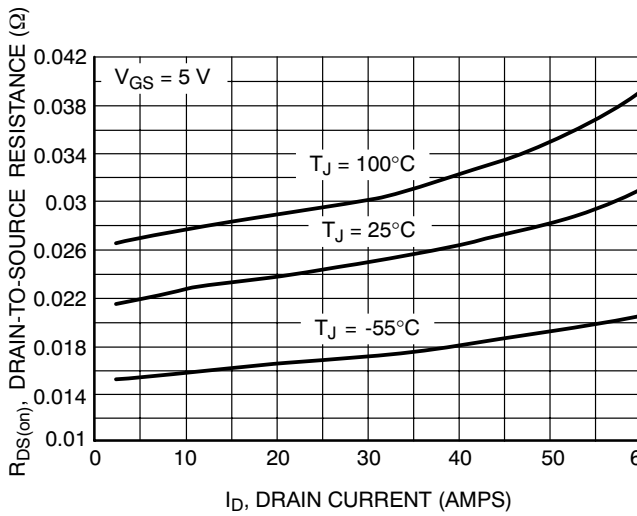


Figure 3. On-Resistance vs. Drain Current

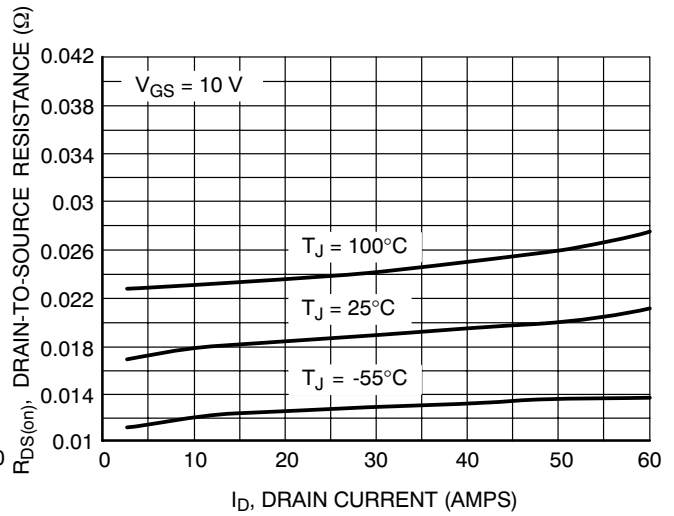


Figure 4. On-Resistance vs. Drain Current

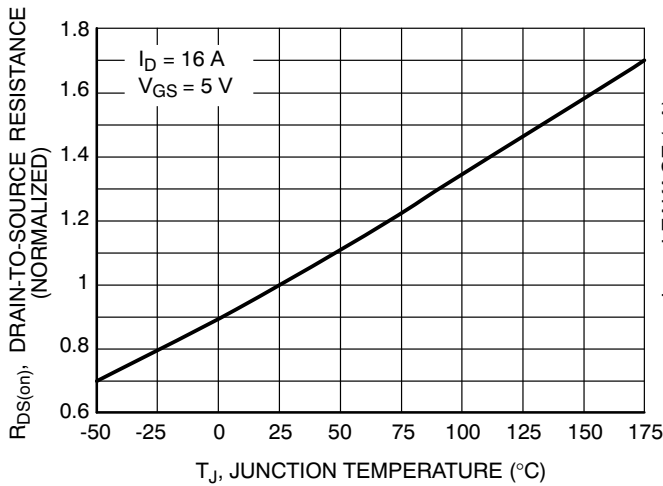


Figure 5. On-Resistance Variation with Temperature

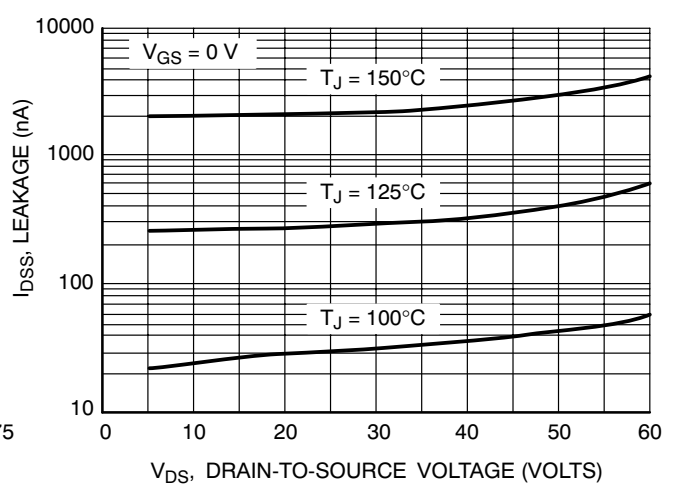


Figure 6. Drain-to-Source Leakage Current vs. Voltage

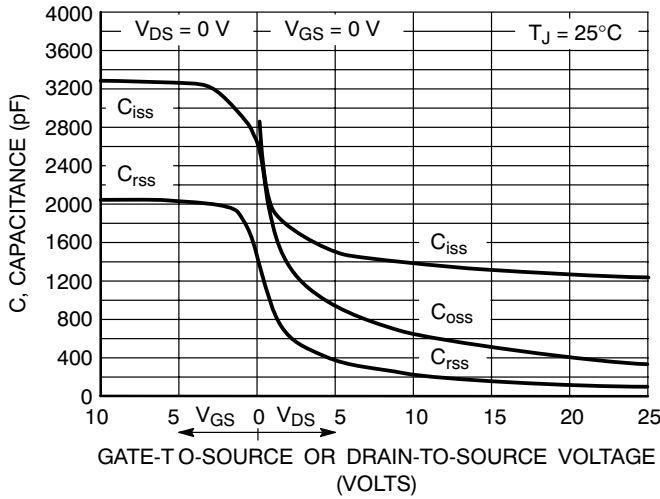


Figure 7. Capacitance Variation

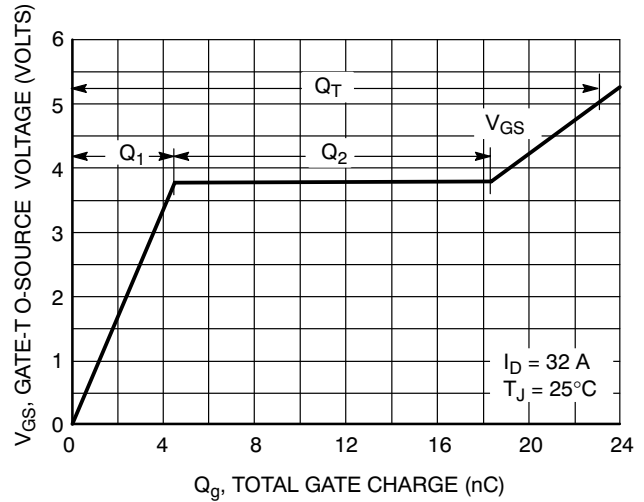


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

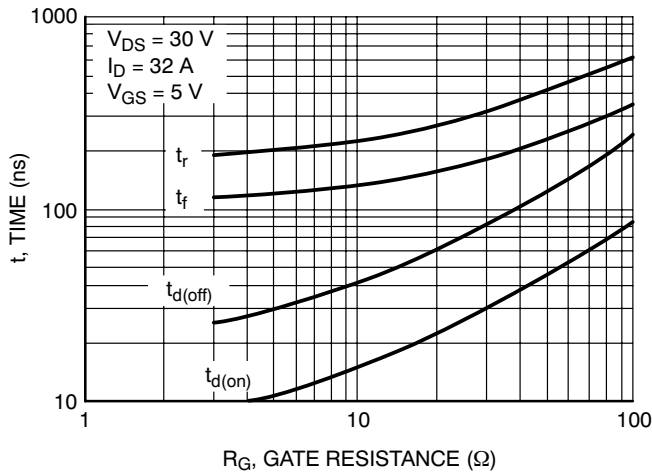


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

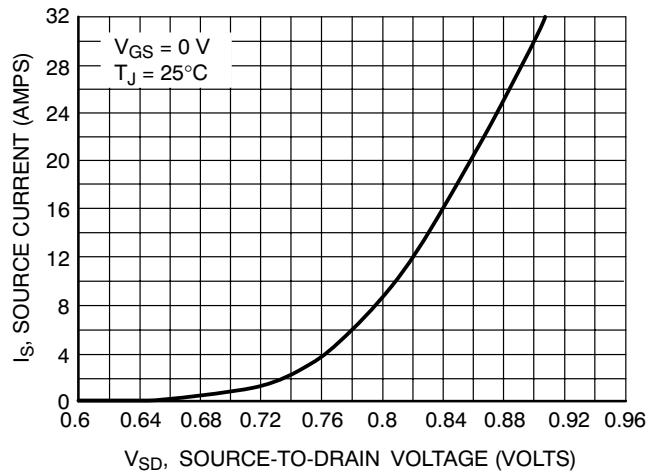


Figure 10. Diode Forward Voltage vs. Current

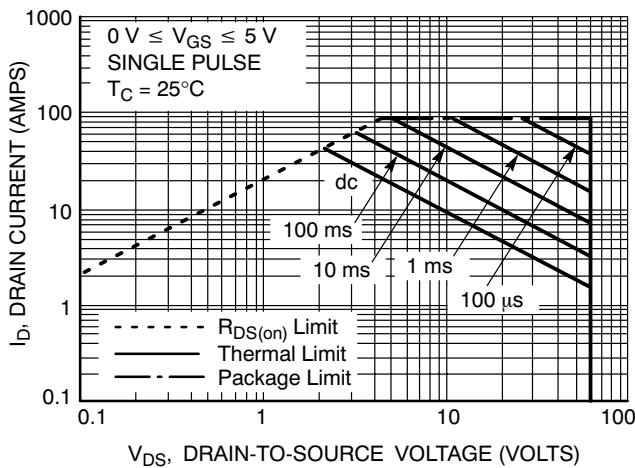


Figure 11. Maximum Rated Forward Biased Safe Operating Area

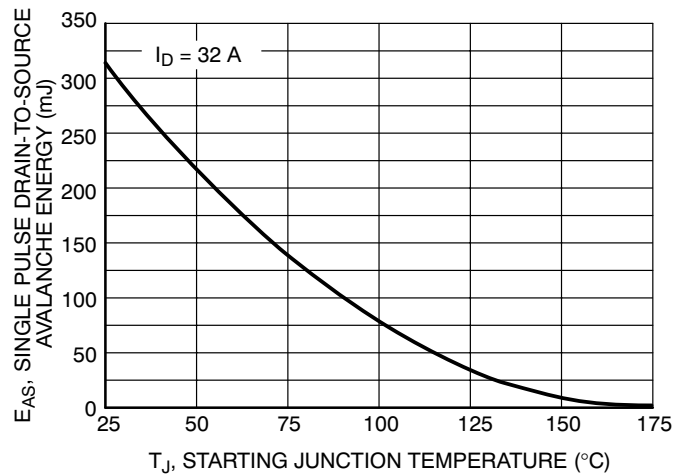


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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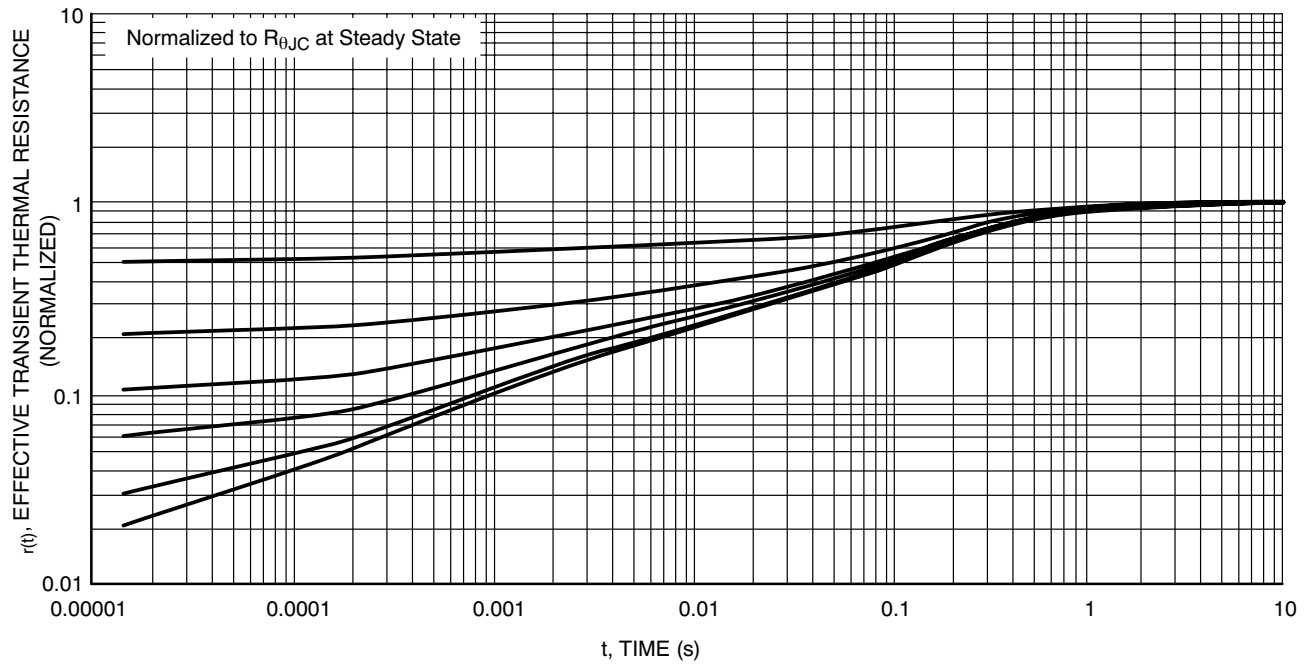


Figure 13. Thermal Response

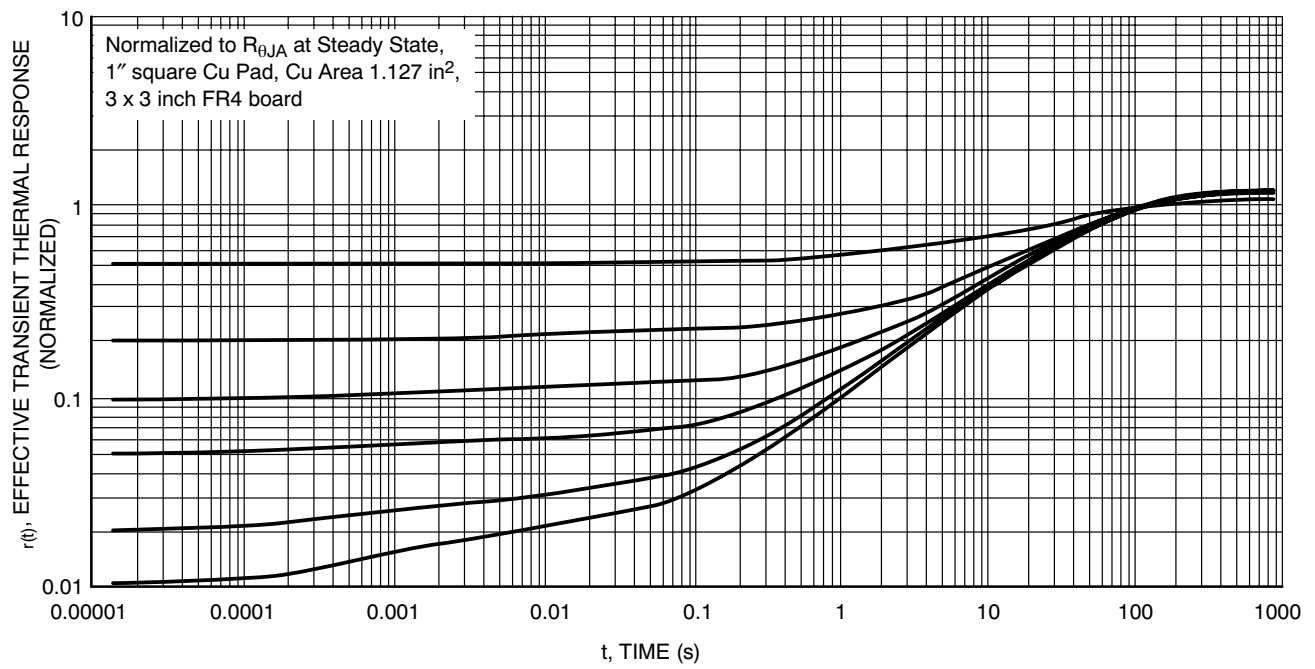
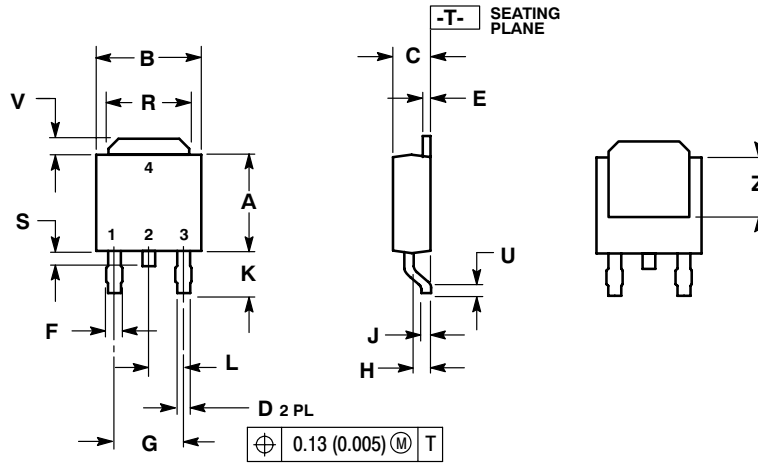


Figure 14. Thermal Response

# NTD32N06L

## PACKAGE DIMENSIONS

DPAK  
CASE 369C-01  
ISSUE O

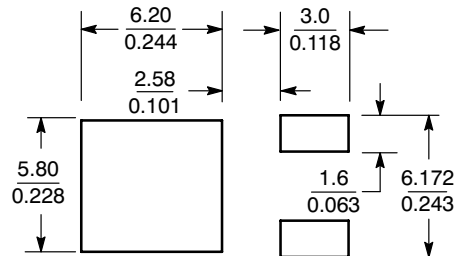


NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

## SOLDERING FOOTPRINT\*



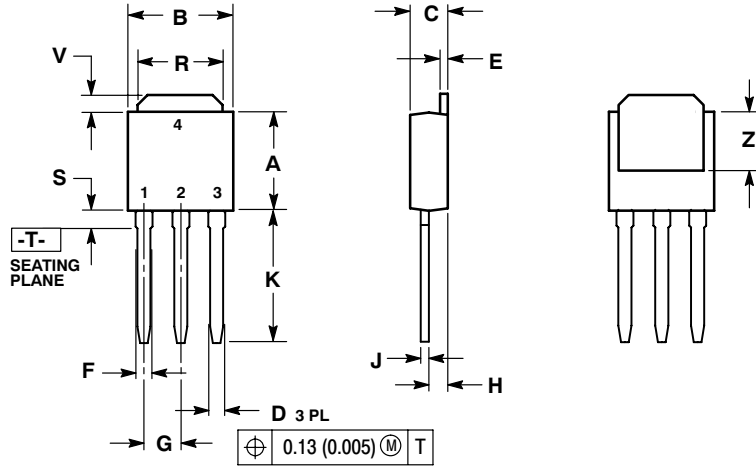
SCALE 3:1 (mm/inches)

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# NTD32N06L

## PACKAGE DIMENSIONS

DPAK  
CASE 369D-01  
ISSUE B



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

### STYLE 2:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

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